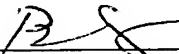


REMARKS

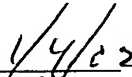
Claims 1-19 are pending after the amendment. No new matter has been added.

Entry of this Preliminary Amendment is respectfully requested.

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on January 4, 2002.



Attorney for Applicant(s)



Date of Signature

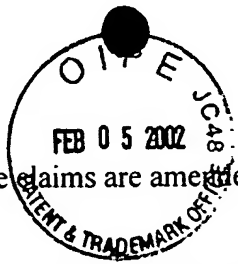
Respectfully submitted,



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ATTACHMENT A

The claims are amended as follows:

15. The method of Claim 1 wherein said varying a flux is part of a deposition sequence for depositing a thin film onto the substrate in the process chamber, the deposition sequence comprising:

introducing a first reactant gas into the chamber;

forming at least one monolayer on the substrate by adsorption of the first reactant gas;

increasing the conductance out of the process region;

decreasing the conductance out of the process region;

introducing at least one ion generating feed gas into the chamber;

generating a plasma from the ion generating feed gas to form ions;

exposing the substrate to the ions;

modulating the ions;

reacting the monolayer with the ions to deposit the thin film;

increasing the conductance out of the process region; and

[evacuating excess ion generating feed gas from the chamber; and]

decreasing the conductance out of the process region.

16. The method of Claim 1 wherein said varying a flux is part of a deposition sequence for depositing a thin film onto the substrate in the process chamber, the deposition sequence comprising:

introducing a first reactant gas into the chamber;

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forming at least one monolayer on the substrate by adsorption of the first reactant gas;

increasing the conductance out of the process region;

decreasing the conductance out of the process region;

introducing at least one reactive atom generating feed gas into the chamber;

generating a plasma from the reactive atom generating feed gas to form reactive atoms;

exposing the substrate to the reactive atoms;

modulating the reactive atoms;

reacting the monolayer with the reactive atoms to deposit the thin film;

increasing the conductance out of the process region; and

[evacuating excess reactive atom generating feed gas from the chamber; and]

decreasing the conductance out of the process region.

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